

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

ATP203

N-Channel Silicon MOSFET General-Purpose Switching Device Applications

Features

- Low ON-resistance
- 4V drive
- Halogen free compliance

Large currentSlim package

Protection diode in

Specifications

Absolute Maximum Ratings at Ta=25°C

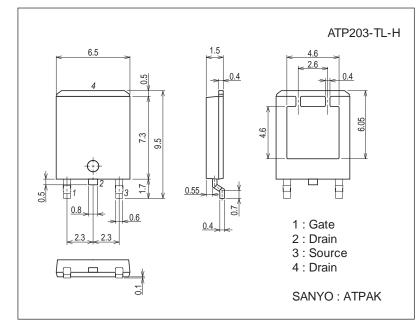
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		75	А
Drain Current (PW≤10µs)	IDP	PW≤10µs, duty cycle≤1%	225	A
Allowable Power Dissipation	PD	Tc=25°C	50	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		52	mJ
Avalanche Current *2	IAV		38	A

Note :*1 V_{DD}=10V, L=50 μ H, I_{AV}=38A

*2 L≤50µH, Single pulse

Package Dimensions

unit : mm (typ) 7057-001



Product & Package Information

- Package : ATPAK
- JEITA, JEDEC
- Minimum Packing Quantity : 3,000 pcs./reel

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Packing Type: TL

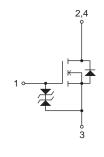


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Electrical Connection

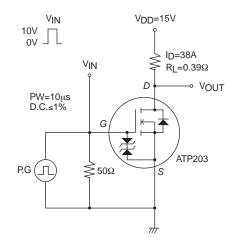


SANYO Semiconductor Co., Ltd. http://semicon.sanyo.com/en/network

Electrical Characteristics at Ta= $25^{\circ}C$

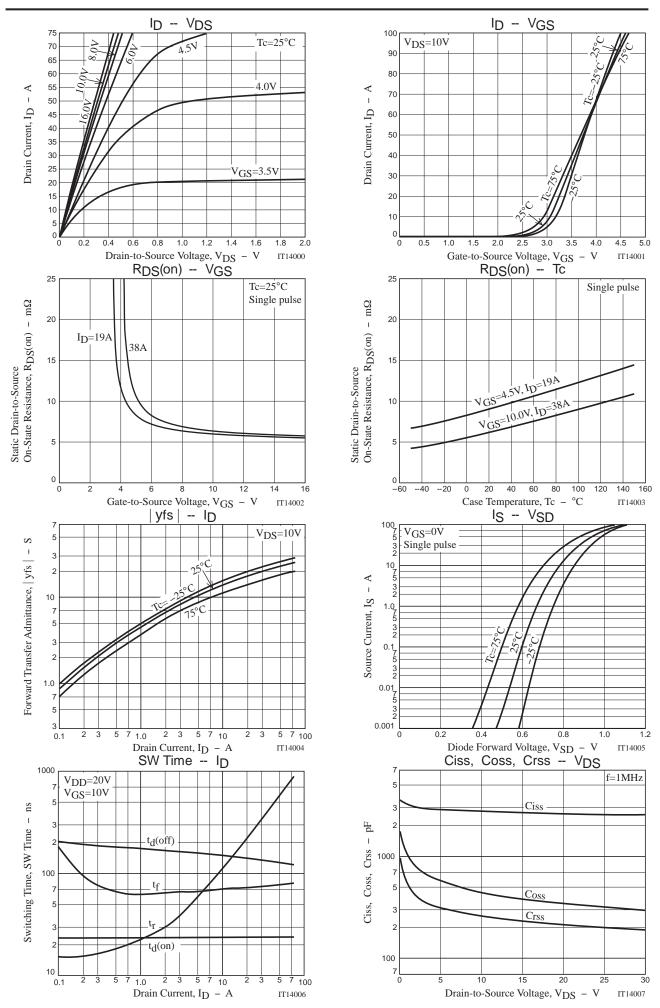
Devementer	Symbol	Conditions	Ratings			1.114
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=38A	13	22		S
Statia Drain to Source On State Desistance	R _{DS} (on)1	ID=38A, VGS=10V		6.3	8.2	mΩ
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	ID=19A, VGS=4.5V		9.5	13.5	mΩ
Input Capacitance	Ciss			2750		pF
Output Capacitance	Coss	VDS=10V, f=1MHz		450		рF
Reverse Transfer Capacitance	Crss			265		рF
Turn-ON Delay Time	t _d (on)			24		ns
Rise Time	tr			420		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		130		ns
Fall Time	tf			75		ns
Total Gate Charge	Qg			44		nC
Gate-to-Source Charge	Qgs	V _{DS} =15V, V _{GS} =10V, I _D =75A		14		nC
Gate-to-Drain "Miller" Charge	Qgd	1		5.6		nC
Diode Forward Voltage	VSD	IS=75A, VGS=0V		1.02	1.2	V

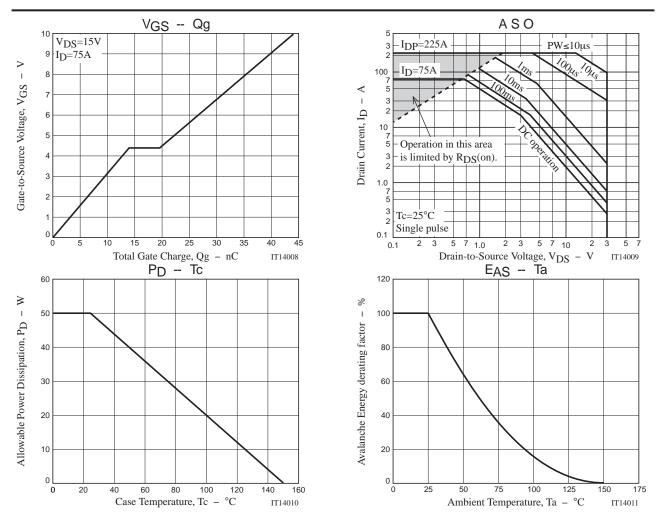
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ATP203-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free



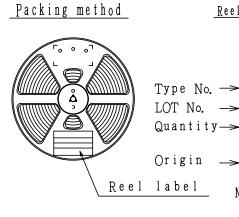


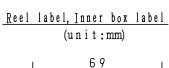
Taping Specification

ATP203-TL-H

1.	Pac	king	Format	(TL)
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Package Name	Carrier Tape	Maximum Number of devices contained (pcs)					Packing f	o r m a t
Lacrage Mame	Type	Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18		
					1 reels contained	5 inner boxes contained		
ATPAK	ATP	3,000	3,000	15,000	Dimensions:mm (external)	Dimensions:mm (external)		
					340×340×28	355×355×165		





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Outer box label It is a label at the time of factory shipments. The form of a label may change in physical distribution process.

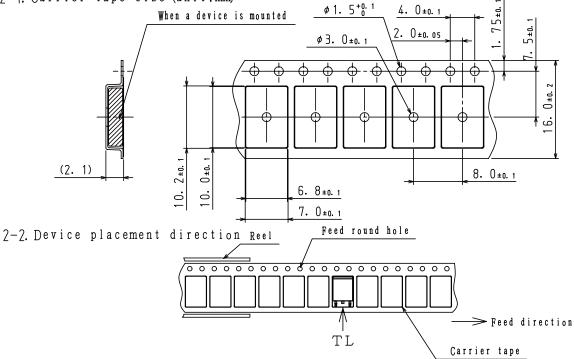
	L	108
		-
	TYPE CODE	*
	TYPB	00000000
0	QTY	0, 000 pcs (1) Lead free #
ω	LOT	00000000
	PACKAGE	00000000
-	SPECIAL	######################################
_	ASSEMBLY:	www. (DIFFUSION: *****)

NOTE (1) The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

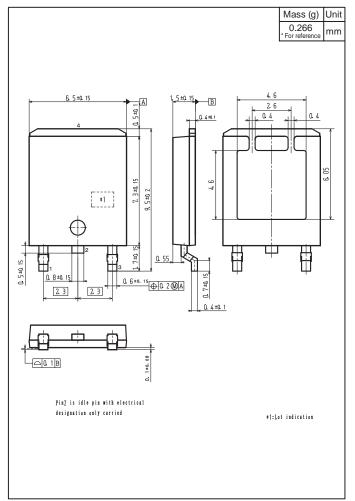
2. Taping configuration

2-1. Carrier tape size (unit:mm)

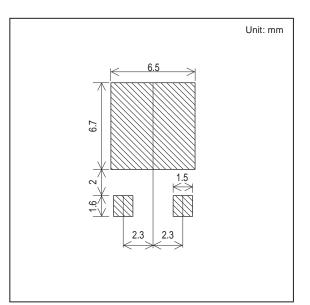


The one erectrode terminals on feed hole side TL

Outline Drawing ATP203-TL-H



Land Pattern Example



Note on usage : Since the ATP203 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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